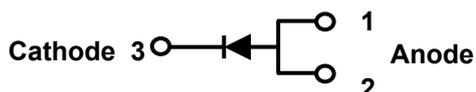
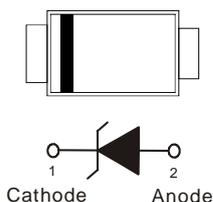


Trench MOS Barrier Schottky Rectifier

SMAF



Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors

Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

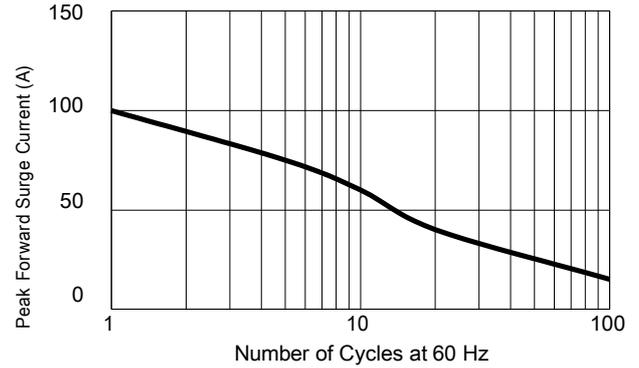
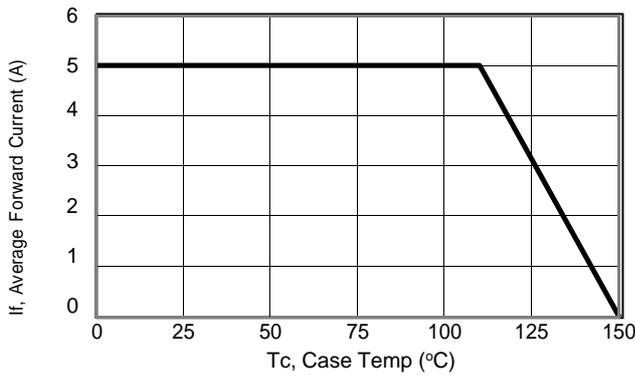
Parameter	Symbol	Limit	Unit		
Maximum repetitive peak reverse voltage	V _{RRM}	100	V		
Maximum average forward rectified current	I _{F(AV)}	5	A		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I _{FSM}	100	A		
Operating junction and storage temperature range	T _J , T _{STG}	-40 to +150	°C		
Typical thermal resistance per diode(Mounted on FR-4 PCB)	R _{θJA}	150	°C/W		
Instantaneous forward voltage per diode	V _{F(1)}	TYP.	MAX.	V	
		I _F =5A T _J =25°C	-		0.78
		I _F =5A T _J =125°C	0.65		0.69
Instantaneous reverse current per diode at rated reverse voltage	I _{R(2)}	T _J =25°C	-	200	uA
		T _J =125°C	5	15	mA

Notes:

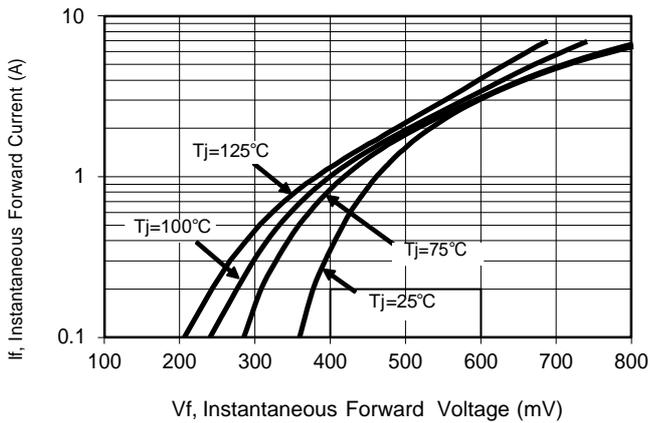
(1) Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

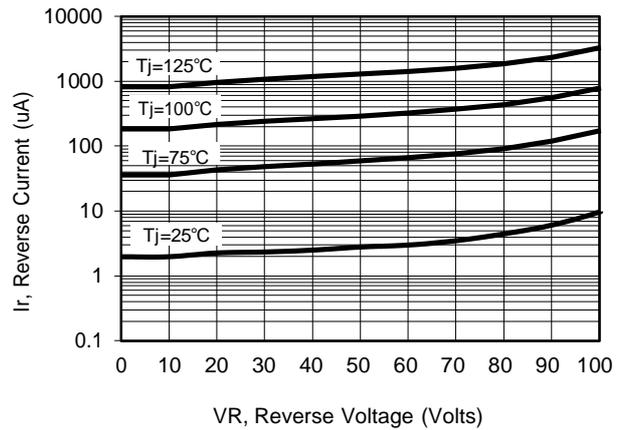
TYPICAL RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



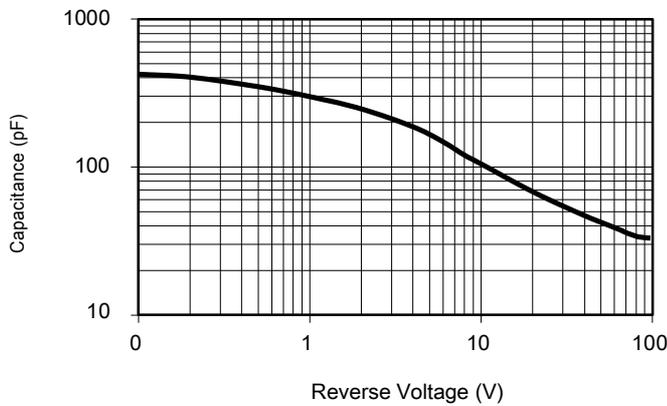
Current Derating, Case



Maximum Repetitive Surge Current



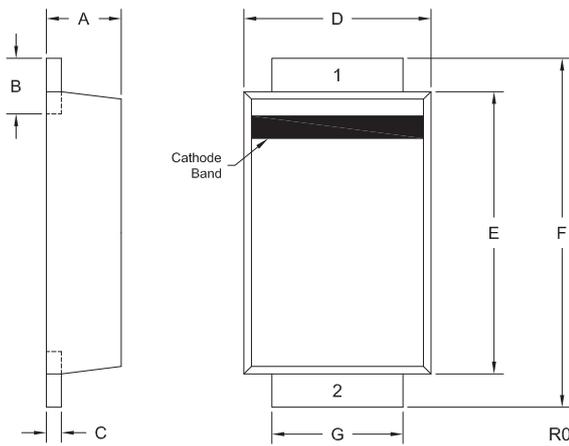
Typical Forward Voltage



Typical Reverse Current

Typical Junction Capacitance

PACKAGE OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.035	0.044	0.90	1.10
B	0.021	0.038	0.55	0.95
C	0.006	0.010	0.15	0.25
D	0.094	0.103	2.40	2.60
E	0.145	0.154	3.70	3.90
F	0.177	0.193	4.50	4.90
G	0.065	0.073	1.65	1.85

SMAFL (REV: R0)